IRF150R, IRF151R, IRF152R, IRF153R

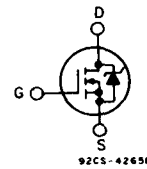
File Number **2002**

Avalanche Energy Rated N-Channel Power MOSFETs

33A and 40A, 60V-100V
$r_{DS}(on) = 0.055\Omega$ and 0.08Ω

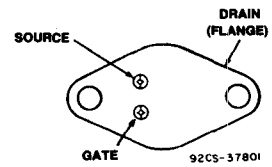
Features:
- *Single pulse avalanche energy rated*
- *SOA is power-dissipation limited*
- *Nanosecond switching speeds*
- *Linear transfer characteristics*
- *High input impedance*

N-CHANNEL ENHANCEMENT MODE



TERMINAL DIAGRAM

TERMINAL DESIGNATION



JEDEC TO - 204 AE

The IRF150R, IRF151R, IRF152R and IRF153R are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. These are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

The IRF-types are supplied in the JEDEC TO-204AE metal package.

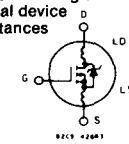
Absolute Maximum Ratings

	Parameter	IRF150R	IRF151R	IRF152R	IRF153R	Units
V_{DS}	Drain - Source Voltage ①	100	60	100	60	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	100	60	100	60	V
I_D @ T_C = 25°C	Continuous Drain Current	40	40	33	33	A
I_D @ T_C = 100°C	Continuous Drain Current	25	25	20	20	A
I_{DM}	Pulsed Drain Current ③	160	160	132	132	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	150 (See Fig. 14)				W
	Linear Derating Factor	1.2 (See Fig. 14)				W/°C
E_{as}	Single Pulse Avalanche Energy Rating ④	150				mj
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @ T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRF150R IRF152R	100	—	—	V	V_{GS} = 0V
		IRF151R IRF153R	60	—	—	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	—	4.0	V	$V_{DS} = V_{GS}$, I_D = 250μ A
I_{GSS}	Gate-Source Leakage Forward	ALL	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-Source Leakage Reverse	ALL	—	—	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			—	—	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRF150R IRF151R	40	—	—	A	$V_{DS} > I_{D(on)} \times R_{DS(on)\,max.}$, V_{GS} = 10V
		IRF152R IRF153R	33	—	—	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRF150R IRF151R	—	0.045	0.055	Ω	V_{GS} = 10V, I_D = 20A
		IRF152R IRF153R	—	0.06	0.08	Ω	
g_{fs}	Forward Transconductance ②	ALL	9.0	11	—	S(℧)	$V_{DS} > I_{D(on)} \times R_{DS(on)max.}$, I_D = 20A
C_{iss}	Input Capacitance	ALL	—	2000	—	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	—	1000	—	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	—	350	—	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	—	—	35	ns	$V_{DD} \simeq$ 24V, I_D = 20A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	—	—	100	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	—	—	125	ns	
t_f	Fall Time	ALL	—	—	100	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	63	120	nC	V_{GS} = 10V, I_D = 50A, V_{DS} = 0.8V Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	—	27	—	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	—	36	—	nC	
L_D	Internal Drain Inductance	ALL	—	5.0	—	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	—	12.5	—	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances

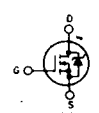


Thermal Resistance

$R_{th}JC$	Junction-to-Case	ALL	—	—	0.83	°C/W	
$R_{th}CS$	Case-to-Sink	ALL	—	0.1	—	°C/W	Mounting surface flat, smooth, and greased.
$R_{th}JA$	Junction-to-Ambient	ALL	—	—	30	°C/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRF150R IRF151R	—	—	40	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRF152R IRF153R	—	—	33	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRF150R IRF151R	—	—	160	A	
		IRF152R IRF153R	—	—	132	A	
V_{SD}	Diode Forward Voltage ②	IRF150R IRF151R	—	—	2.5	V	T_C = 25°C, I_S = 40A, V_{GS} = 0V
		IRF152R IRF153R	—	—	2.3	V	T_C = 25°C, I_S = 33A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	—	600	—	ns	T_J = 150°C, I_F = 40A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	—	3.3	—	μC	T_J = 150°C, I_F = 40A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				



① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%.
③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).
④ V_{DD} = 10V, starting T_J = 25°C, L = 170μH, R_{gs} = 50Ω, I_{peak} = 40A. See figures 15, 16.

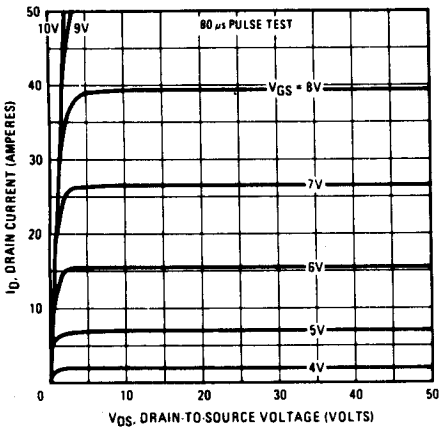


Fig. 1 – Typical Output Characteristics

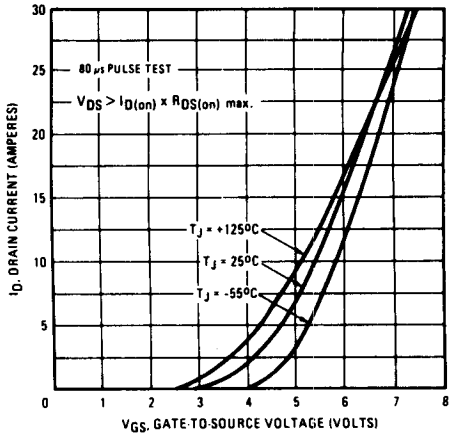


Fig. 2 – Typical Transfer Characteristics

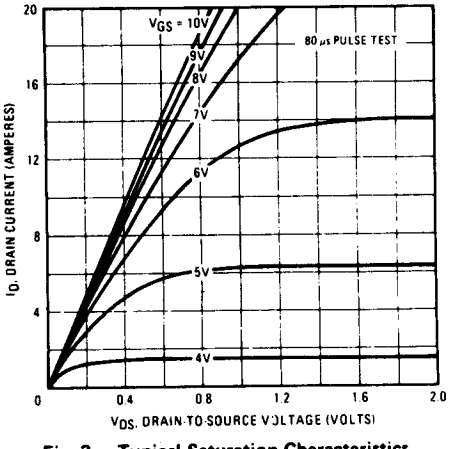


Fig. 3 – Typical Saturation Characteristics

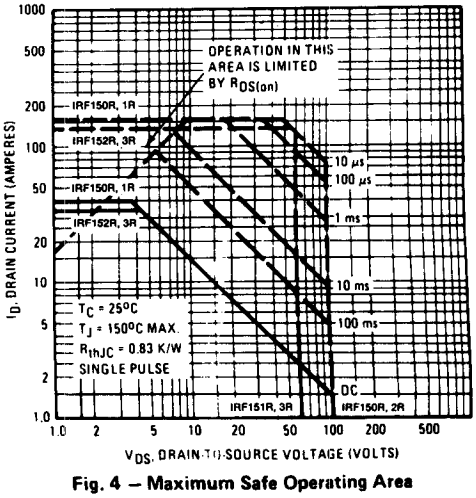


Fig. 4 – Maximum Safe Operating Area

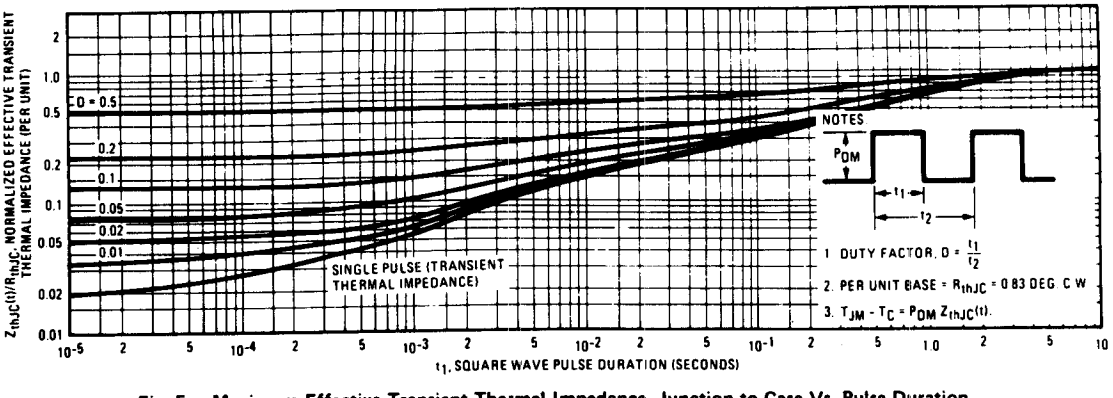


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

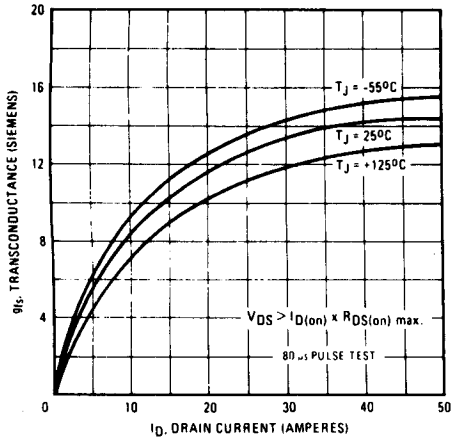


Fig. 6 – Typical Transconductance Vs. Drain Current

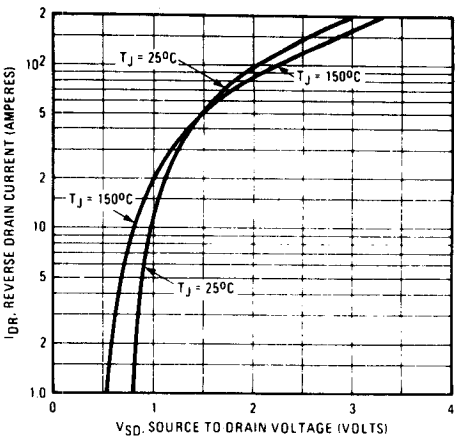


Fig. 7 – Typical Source-Drain Diode Forward Voltage

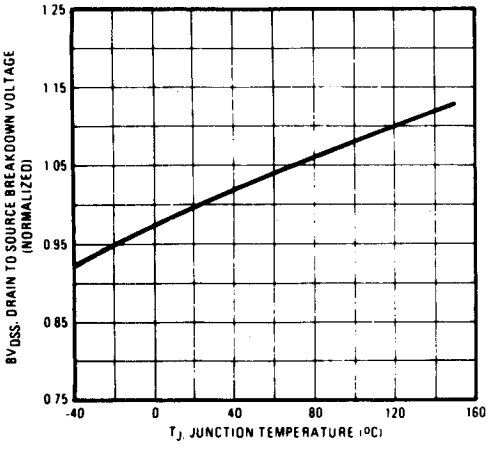


Fig. 8 – Breakdown Voltage Vs. Temperature

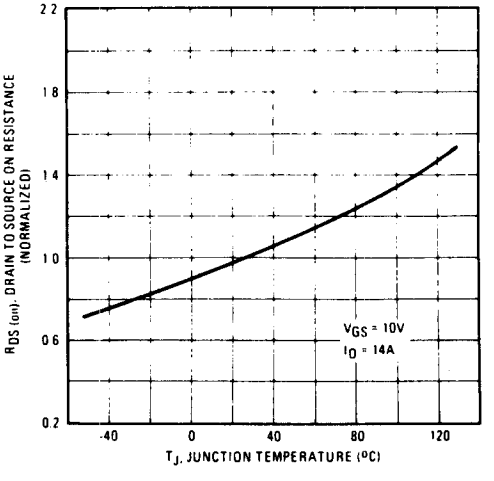


Fig. 9 – Normalized On-Resistance Vs. Temperature

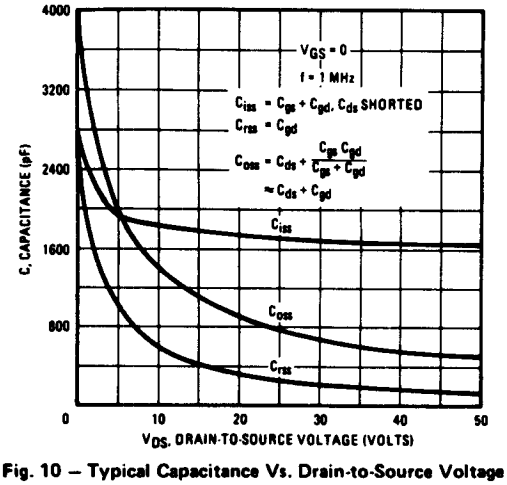


Fig. 10 – Typical Capacitance Vs. Drain-to-Source Voltage

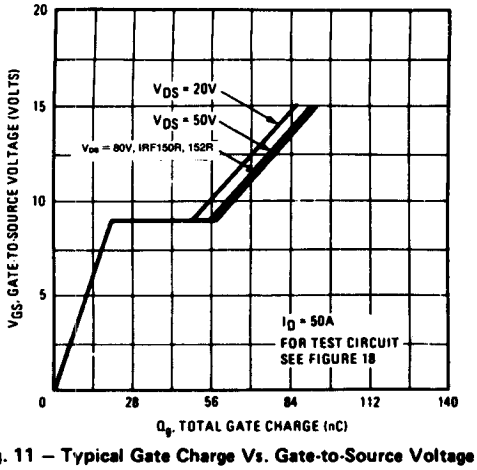


Fig. 11 – Typical Gate Charge Vs. Gate-to-Source Voltage

IRF150R, IRF151R, IRF152R, IRF153R

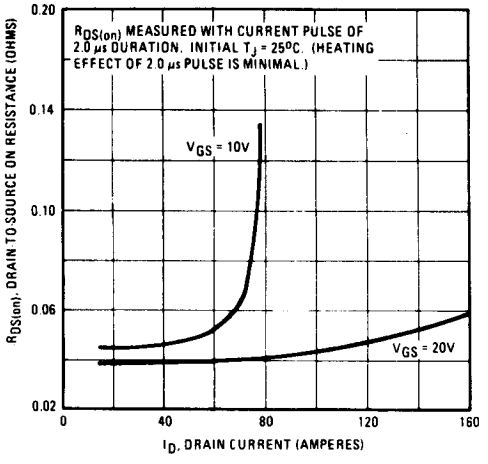


Fig. 12 — Typical On-Resistance Vs. Drain Current

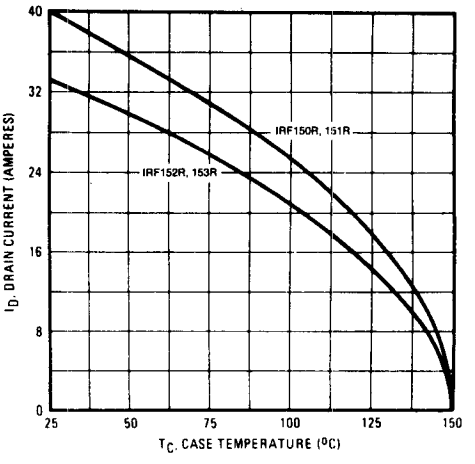


Fig. 13 — Maximum Drain Current Vs. Case Temperature

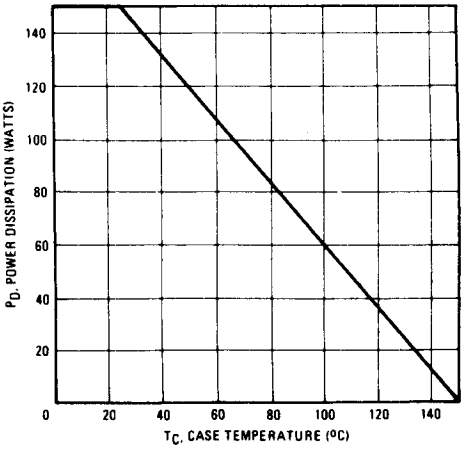


Fig. 14 — Power Vs. Temperature Derating Curve

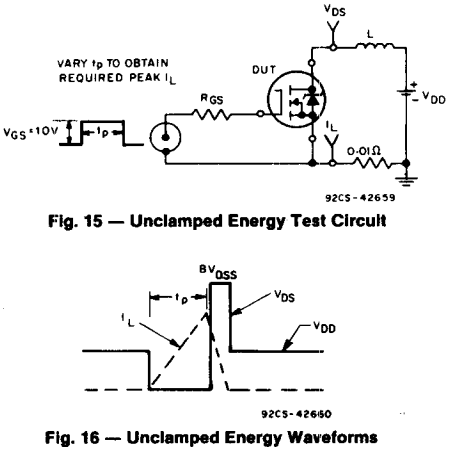


Fig. 15 — Unclamped Energy Test Circuit

Fig. 16 — Unclamped Energy Waveforms

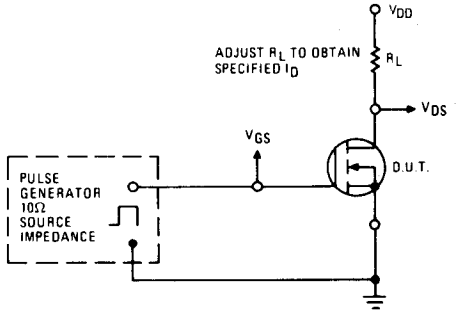


Fig. 17 — Switching Time Test Circuit

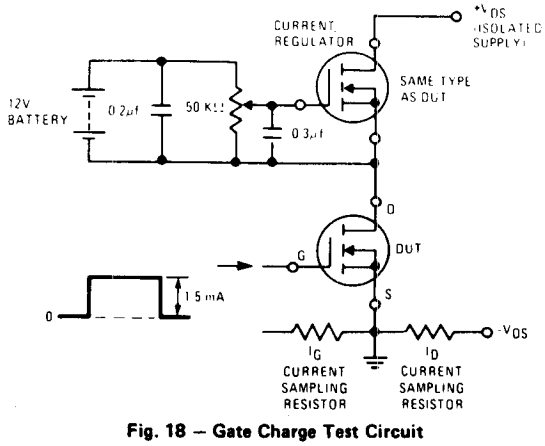


Fig. 18 — Gate Charge Test Circuit